



PTO/SB/08A (10-01)

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Substitute for form 1449/PTO				Complete if known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/665,757
(use as many sheets as necessary)				Filing Date	September 19, 2003
				First Named Inventor	Glenn J. Leedy
				Art Unit	2822
				Examiner Name	Pamela E. Perkins
Sheet 1		of 2	Attorney Docket Number ELM-1 CONT.9		

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Examiner Initials ¹	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Documents	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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				Examiner Name	Pamela E. Perkins
Sheet	2	of	2	Attorney Docket Number	ELM-1 CONT.9

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Examiner initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ⁴
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Examiner Signature	<i>Phillip J. Leedy</i>	Date Considered	4/28/00
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All References Have Been Considered:

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